Small Signal MOSFET

20 V, 200 mA, Dual N-Channel, 1.0 mm x 1.0 mm SOT-963 Package

Features

- Dual N-Channel MOSFET
- Offers a Low $R_{DS(ON)}$ Solution in the Ultra Small 1.0 x 1.0 mm Package
- 1.5 V Gate Voltage Rating
- Ultra Thin Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics
- These are Pb-Free Devices

Applications

- General Purpose Interfacing Switch
- Optimized for Power Management in Ultra Portable Equipment

MAXIMUM RATINGS (T_J = 25° C unless otherwise specified)

Para	Symbol	Value	Unit			
Drain-to-Source Voltag	V _{DSS}	20	V			
Gate-to-Source Voltag	е		V _{GS}	±8	V	
Continuous Drain	Steady	$T_A = 25^{\circ}C$		160		
Current (Note 1)	State	$T_A = 85^{\circ}C$	Ι _D	115	mA	
	$t \le 5 s$	$T_A = 25^{\circ}C$		200		
Power Dissipation	Steady State	T _A = 25°C	P _D	125		
(Note 1)					mW	
	t ≤ 5 s			200		
Pulsed Drain Current	I _{DM}	800	mA			
Operating Junction and	T _J , T _{STG}	-55 to 150	°C			
	ISIG	100				
Source Current (Body D	۱ _S	200	mA			
Lead Temperature for S (1/8" from case for 1	ΤL	260	°C			

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

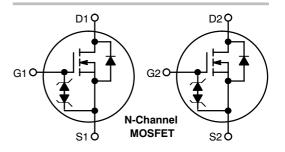
2. Pulse Test: pulse width \leq 300 μ s, duty cycle \leq 2%

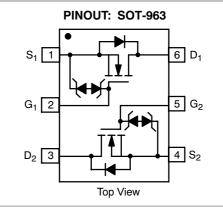


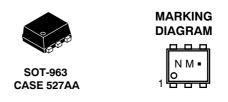
ON Semiconductor®

http://onsemi.com

V _{(BR)DSS}	R _{DS(ON)} MAX	I _D Max
	3.0 Ω @ 4.5 V	
20 V	4.0 Ω @ 2.5 V	0.2 A
	6.0 Ω @ 1.8 V	
	10 Ω @ 1.5 V	









= Date Code

N M

= Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Мах	Unit
Junction-to-Ambient – Steady State (Note 3)	Paul	1000	°C/W
Junction-to-Ambient $- t = 5 s$ (Note 3)	$R_{\theta JA}$	600	0/11

3. Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

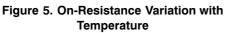
ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS		-		•	•	• •	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 V, I_D = 250 \mu A$		20			V
Zero Gate Voltage Drain Current		V _{GS} = 0 V, V _{DS} = 5 V	$T_J = 25^{\circ}C$			50	nA
	I _{DSS}		T _J = 85°C			200	
		V_{GS} = 0 V, V_{DS} = 16 V	T _J = 25°C			100	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} =	±5.0 V			100	nA
ON CHARACTERISTICS (Note 4)	-						
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_D = 2$	250 μA	0.4		1.0	V
Drain-to-Source On Resistance		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 100 \text{ mA}$			1.5	3.0	Ω
		V_{GS} = 2.5 V, I _D = 50 mA			2.0	4.0	
	R _{DS(ON)}	V _{GS} = 1.8 V, I _D = 20 mA			3.0	6.0	
		V _{GS} = 1.5 V, I _D = 10 mA			4.0	10	
		V _{GS} = 1.2 V, I _D = 1.0 mA			5.5		
Forward Transconductance	g fs	V _{DS} = 5.0 V, I _D = 125 mA			0.35		S
Source-Drain Diode Voltage	V _{SD}	V _{GS} = 0 V, I _D = 10 mA			0.6	1.0	V
CHARGES, CAPACITANCES AND GATE	RESISTANCE						
Input Capacitance	C _{ISS}	f = 1.0 MHz, V _{GS} = 0 V V _{DS} = 15 V			9.0		pF
Output Capacitance	C _{OSS}				3.0		
Reverse Transfer Capacitance	C _{RSS}				2.2		
SWITCHING CHARACTERISTICS, $V_{GS} =$	4.5 V (Note 4)						
Turn-On Delay Time	t _{d(ON)}	V_{GS} = 4.5 V, V_{DD} = 10 V, I_{D} = 200 mA, R_{G} = 2.0 Ω			15		- ns
Rise Time	t _r				24		
Turn-Off Delay Time	t _{d(OFF)}				90		
Fall Time	t _f				60		

4. Switching characteristics are independent of operating junction temperatures.

0.4 0.4 ' TJ = 25°C $V_{GS} = 3$ V to 5 V $V_{DS} \ge 5 V$ T_{.1} = 125°C ID, DRAIN CURRENT (AMPS) ID, DRAIN CURRENT (AMPS) 2.5 V $T_J = -55^{\circ}C$ 2.0 V 0.3 T_{.1} = 25°C 0.3 0.2 0.2 1.5 V 0.1 0.1 1.0 V 0 0 0 5 2 3 5 4 0 2 3 1 1 4 V_{GS}, GATE-T O-SOURCE VOLTAGE (VOLTS) V_{DS}, DRAIN-TO-SOURCE VOLTAGE (VOLTS) **Figure 2. Transfer Characteristics** Figure 1. On-Region Characteristics R_{DS(on)}, DRAIN-T O-SOURCE RESISTANCE (Q) R_{DS(on)}, DRAIN-T O-SOURCE RESISTANCE (Q) 2.5 15 I_D = 200 mA $T_J = 25^{\circ}C$ T_J = 25°C V_{GS} = 2.5 V 2.0 10 1.5 V_{GS} = 4.5 V 1.0 5 0.5 0 0 1 2 3 4 5 0 0.05 0.1 0.15 0.2 0.25 0.3 0.35 0.4 V_{GS}, GATE-T O-SOURCE VOLTAGE (VOLTS) ID. DRAIN CURRENT (AMPS) Figure 4. On-Resistance vs. Drain Current and Figure 3. On-Resistance vs. Gate Voltage **Gate Voltage** 1.75 1000 $V_{GS} = 0 V$ I_D = 200 mA R_{DS(on)}, DRAIN-T O-SOURCE RESISTANCE (NORMALIZED) 92 0.0 22 10 52 0.0 52 10 V_{GS} = 4.5 V T_J = 150°C IDSS, LEAKAGE (nA) 100 T_J = 125°C 10 0 1 8 -50 -25 0 25 50 75 100 125 150 0 4 12 16 20 T_J, JUNCTION TEMPERATURE (°C) V_{DS}, DRAIN-TO-SOURCE VOLTAGE (VOLTS)

TYPICAL PERFORMANCE CURVES







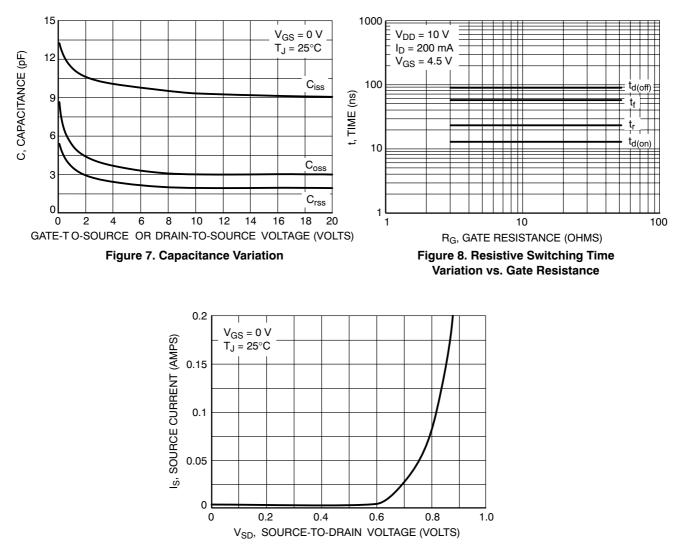


Figure 9. Diode Forward Voltage vs. Current

ORDERING INFORMATION

Device	Package	Shipping [†]
NTUD3128NT5G	SOT-963 (Pb-Free)	8000 / Tape & Reel

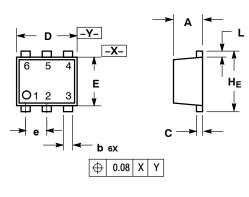
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

semi

SCALE 4:1

SOT-963 CASE 527AA ISSUE D

DATE 30 JUL 2008



2. BASE 1 3. COLLECTOR 2 4. EMITTER 2 5. BASE 2 6. COLLECTOR 1	4. COLLECTOR 2 5. BASE 1 6. COLLECTOR 1	5. CATHODE 2
	2. CATHODE 3. ANODE 4. ANODE 5. CATHODE 6. CATHODE	STYLE 6: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 7: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. ANODE 6. CATHODE	STYLE 8: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 9: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1
STYLE 10: PIN 1. CATHODE 1 2. N/C 3. CATHODE 2 4. ANODE 2 5. N/C 6. ANODE 1		

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI

Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETERS MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS 2. З.

IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.40	0.45	0.50	0.016	0.018	0.020
b	0.10	0.15	0.20	0.004	0.006	0.008
С	0.05	0.10	0.15	0.002	0.004	0.006
D	0.95	1.00	1.05	0.037	0.039	0.041
Е	0.75	0.80	0.85	0.03	0.032	0.034
е	0.35 BSC		().014 BS	C	
L	0.05	0.10	0.15	0.002	0.004	0.006
ΗE	0.95	1.00	1.05	0.037	0.039	0.041

GENERIC **MARKING DIAGRAM***

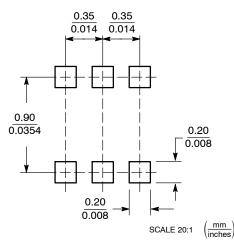


Х = Specific Device Code = Month Code Μ

*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " .",

may or may not be present. SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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